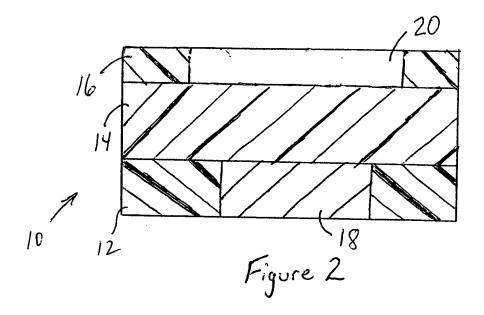
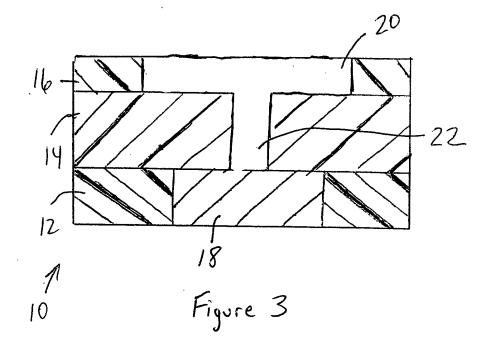
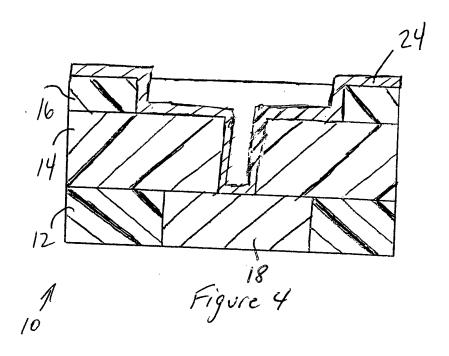
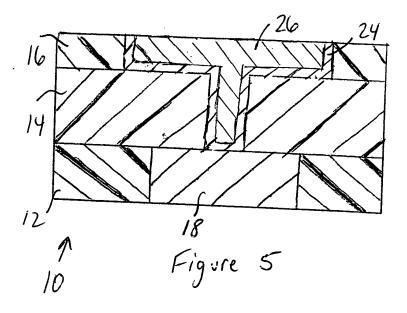


Figure 1









Provide a substrate consisting of multiple dielectric layers with a copper deposit or wiring being provided in one or more of the layers Form a trench in one of the layers, preferably the top layer Form a via in one or more of the lower layers, such as in the trench that has been formed, to the copper deposit Deposit one or more intermediate liners, such as a single liner of Ta/TaN, such as by using a conventional PVD technique Deposit an interconnect liner of aluminum-0.5% copper alloy, such as by using a conventional PVD technique Deposit copper and polish, such as by using conventional CMP techniques

Figure 6

